



1

2

3

4

5

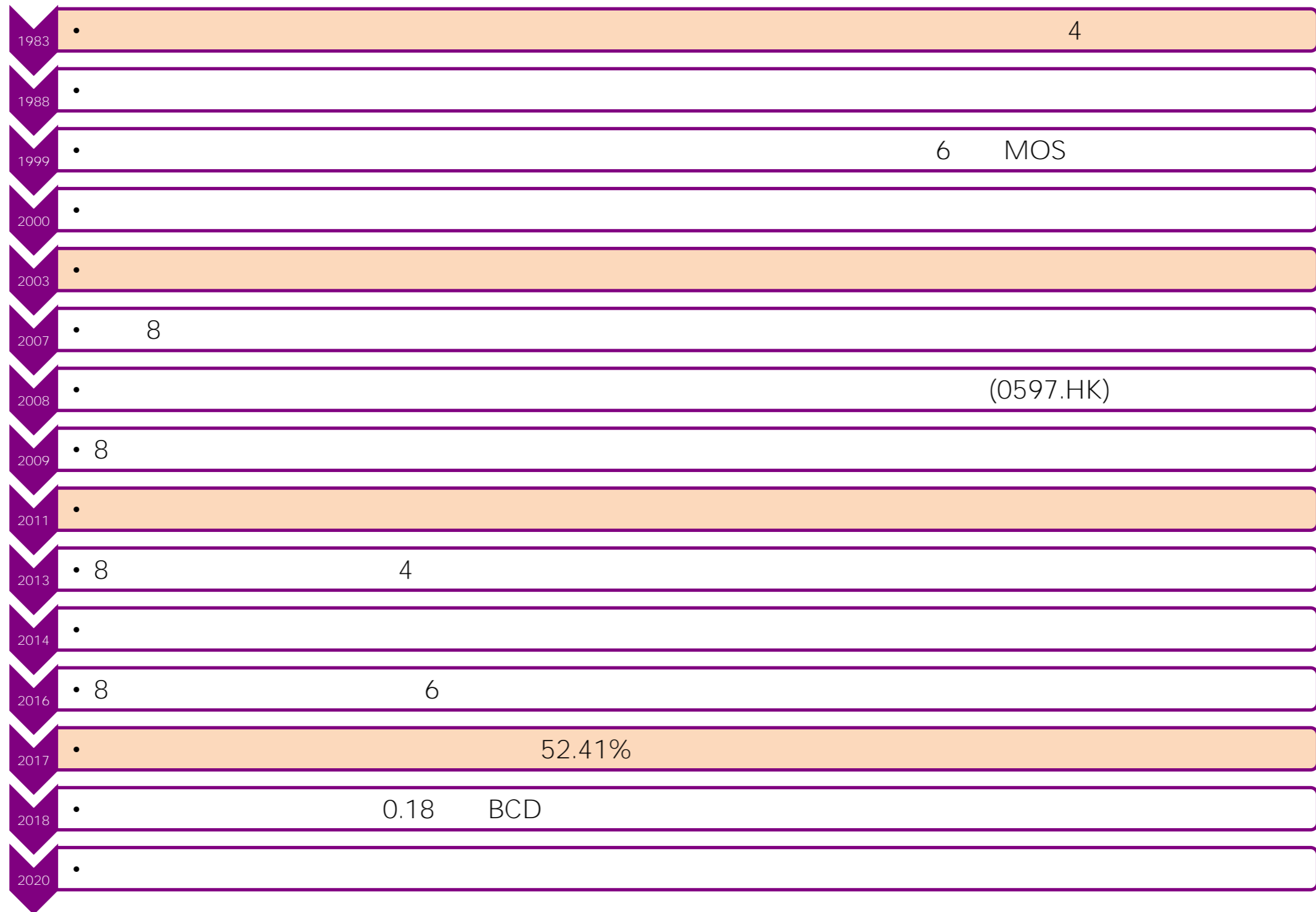
1

IDM

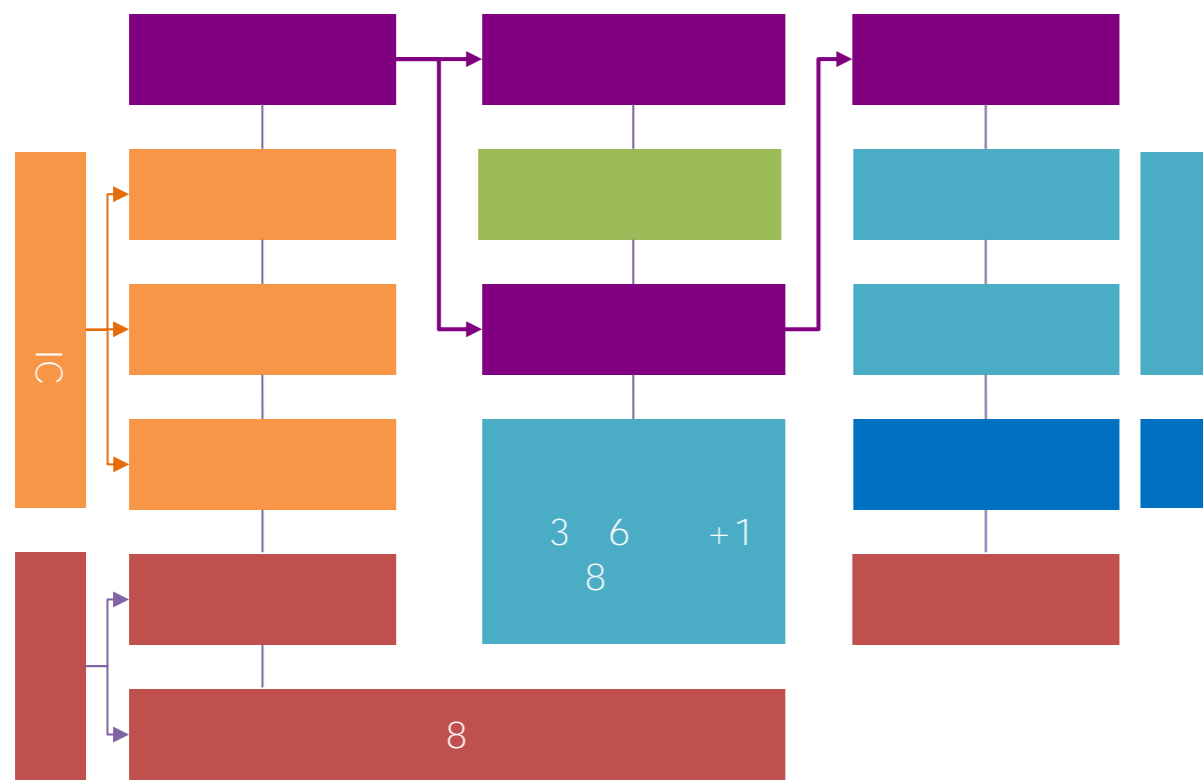
IDM

IDM

IDM



IDM



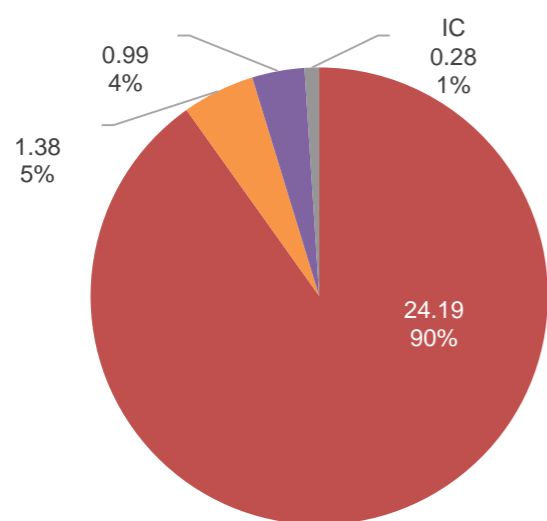
			2018
	3 6	Analog BCD MEMS DMOS Power Discrete	247
	1 8	Advance BCD Analog DMOS	



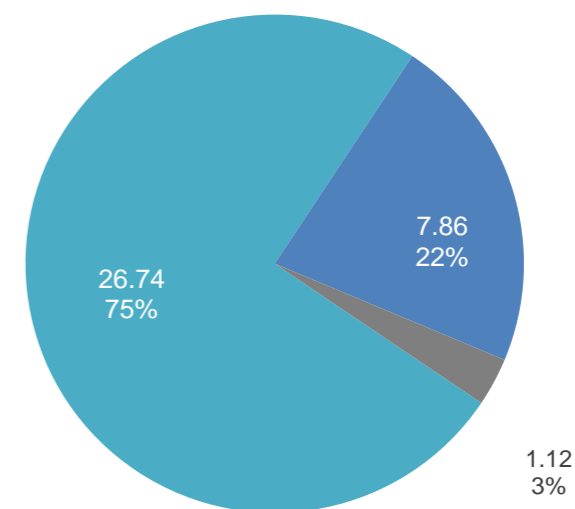
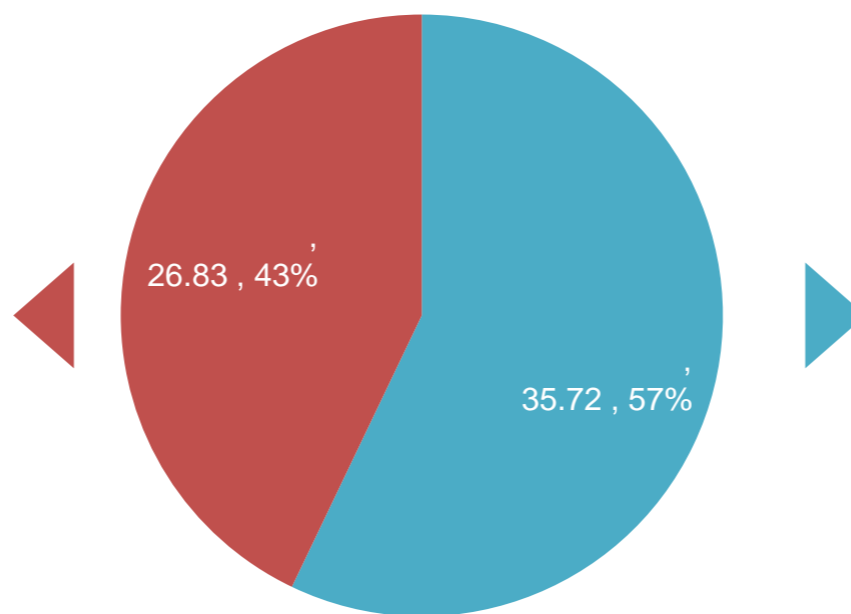
IDM

IDM
TCL MPS

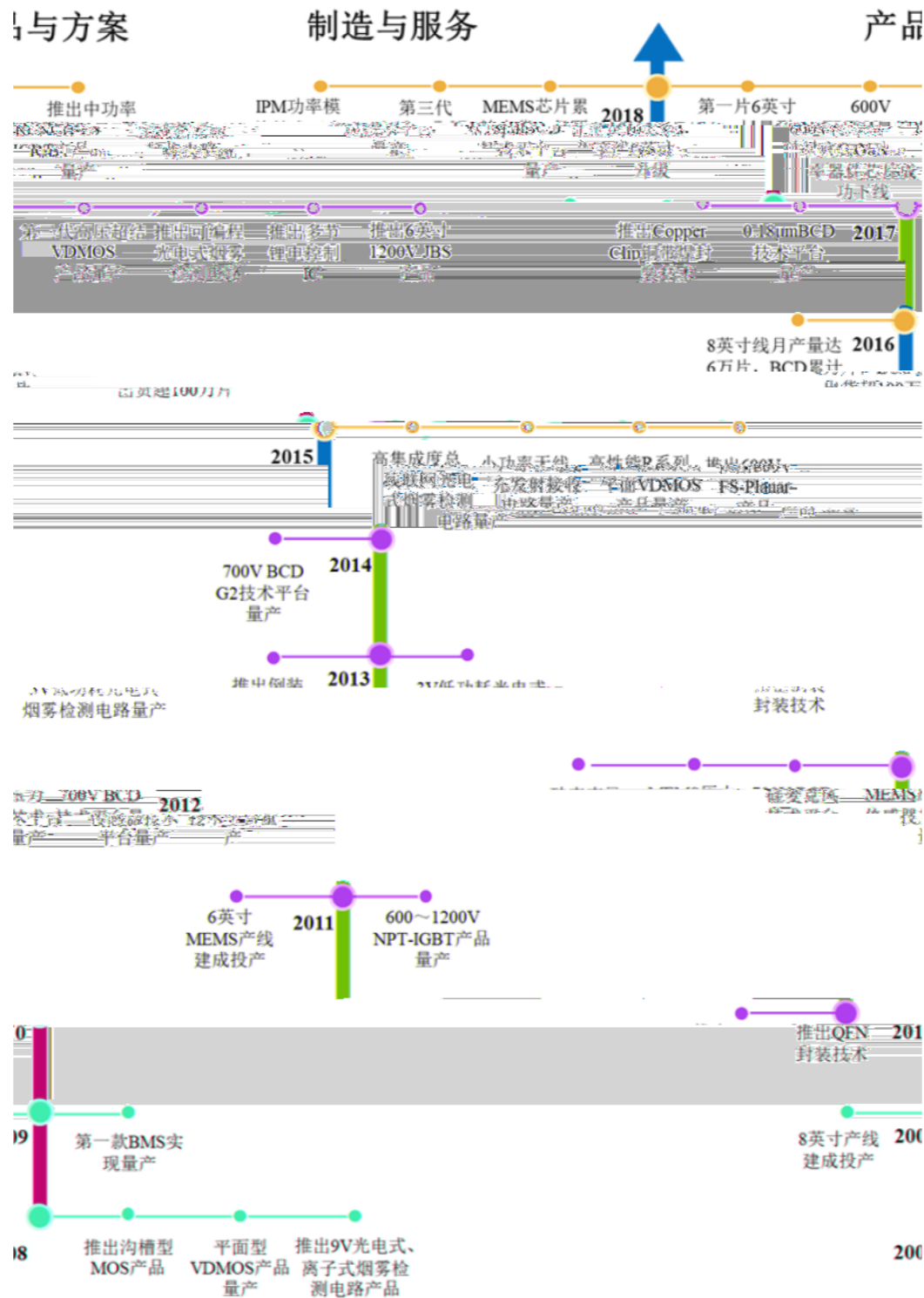
2018



wind



2008年-2018年公司关键产品与工艺发展情况



1

IDM

MOSFET

IGBT SBD FRD

2

1 8 3 6
 SOI BCD
 IGBT MEMS GaN SiC
 1 8

1.0-0.11μm
 CMOS CMOS Bipolar BiCMOS

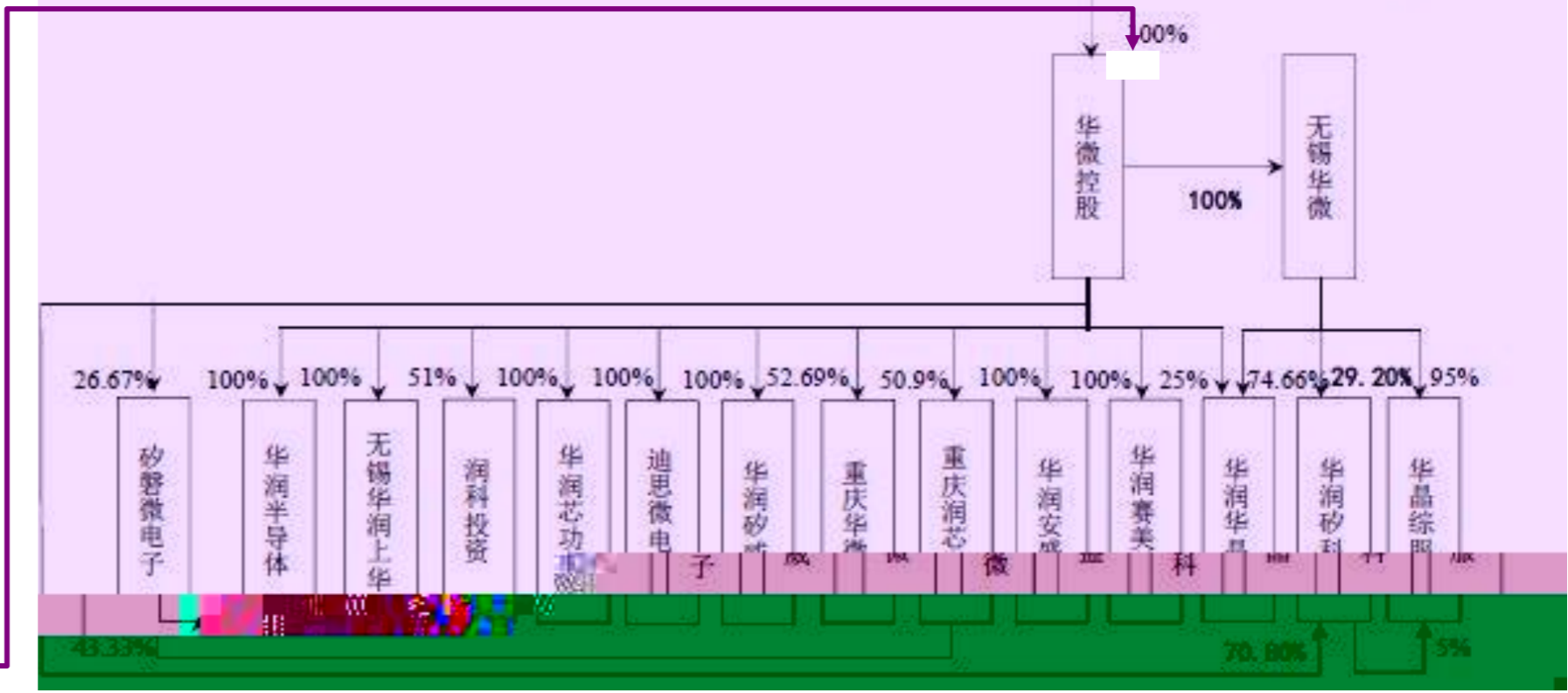
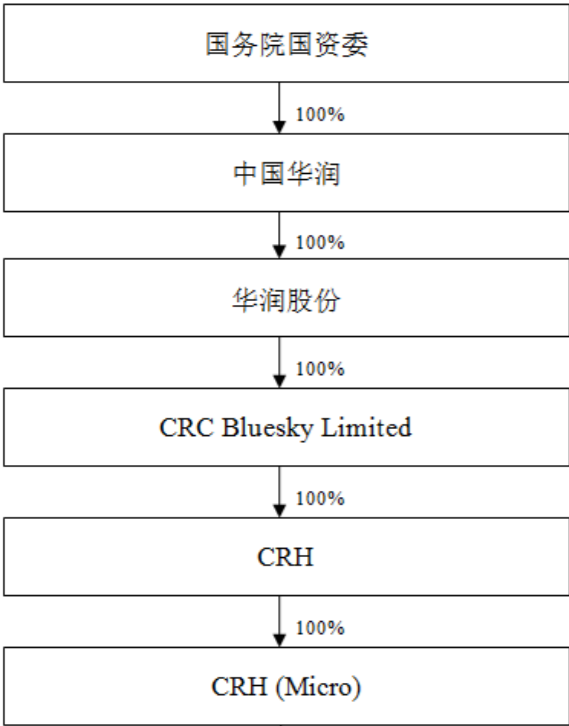
IC

			2018
	3 6	Analog BCD MEMS DMOS Power Discrete	247
	1 8	Advance BCD Analog DMOS	73
	1 8	MOS MOS MOS SBD	60
			199
		QFP QFN PQFN FC-QFN TSSOP SSOP MSOP IPM	62
			69
			2.4



100%

202001



2

2019Q1-3	41.32	2.70
2019Q1-3	22.38%	8.58%
	4.50	36.93%

2019Q1-3

41.32

2.70

2017

2018

14.73%

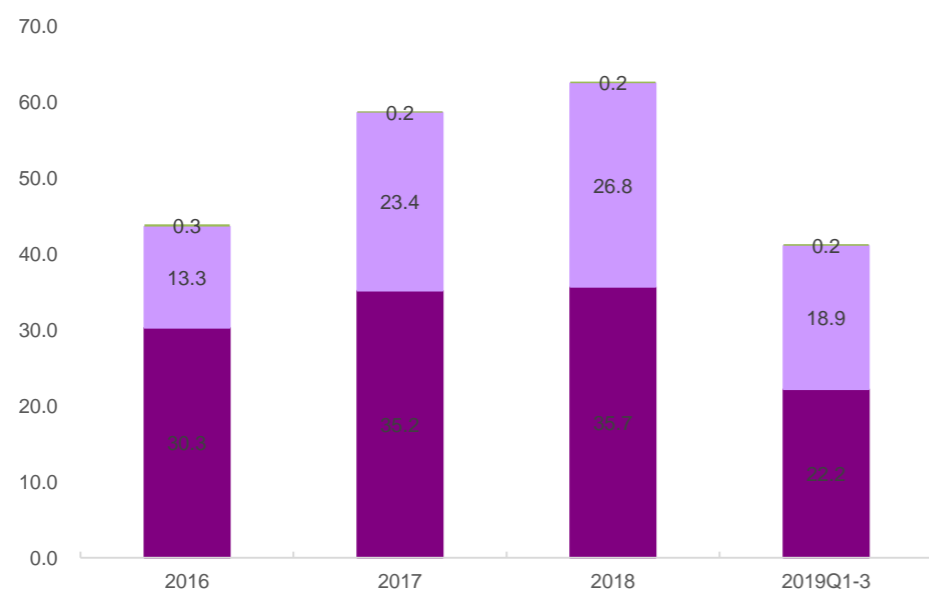
1.48%

2019H1

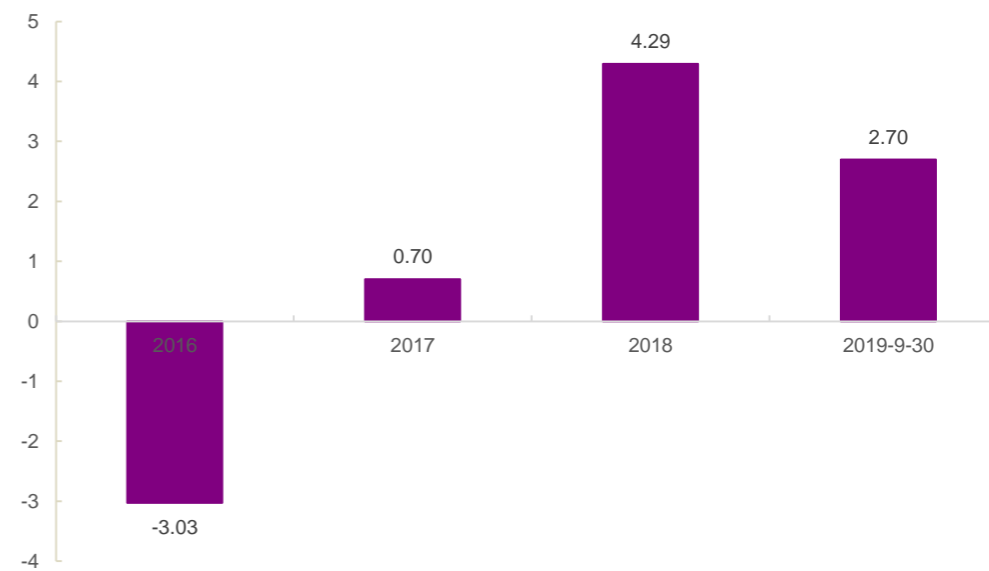
2019Q1-3

41.32

2.70



wind



wind

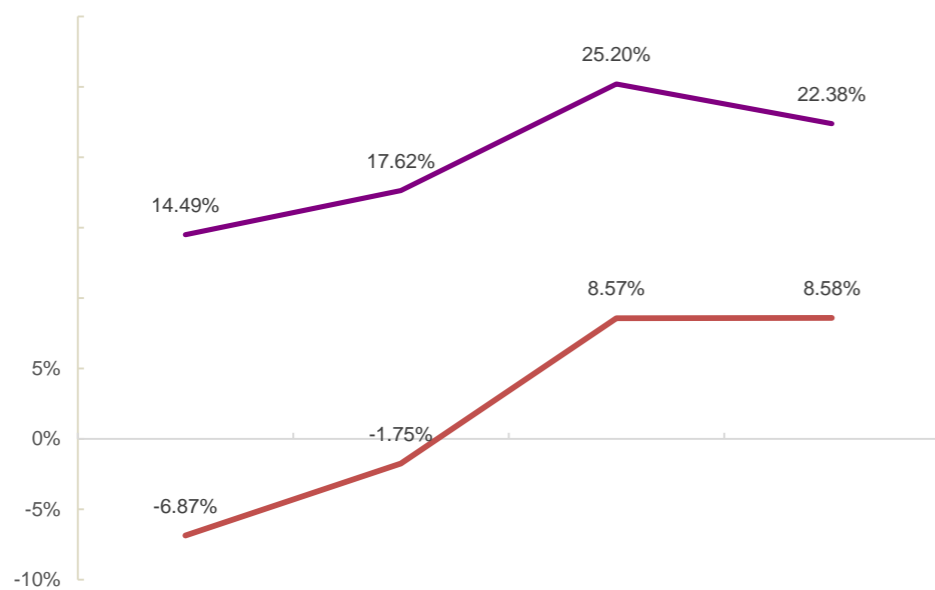
2019Q1-3

22.38%

8.58%

2018
2018

2017
2017 3.49



wind

wind



		2018	2017
	8	184,311.28	180,873.09
	8	397,317.05	387,233.01
	6	149,987.39	150,333.55
	6 1	84,667.33	78,746.57
	6 2	52,562.94	58,083.76
		45,152.93	45,346.07
		119,878.92	111,623.56
		23,639.78	21,216.57
		17,854.81	17,172.57
	8	24.91%	31.23%
	8	19.94%	25.09%
	6	15.52%	15.73%
	6 1	27.25%	27.21%
	6 2	9.61%	12.89%
		23.56%	25.31%
		36.81%	38.12%
		42.09%	44.36%
		33.60%	38.33%
	8	13,409.48	38,832.46
	8	27,620.75	38,700.45
	6	2,957.87	3,549.41
	6 1	4,468.50	4,501.33
	6 2	1,215.46	1,972.54
		2,530.98	2,455.20
		7,873.66	7,103.02
		1,873.14	1,738.79
		1,264.87	1,467.87
		63,214.71	100,321.07

2018 2017

2018

2017 37,106.36

2018 25,422.98

8

2017 2018

11,079.70

2018 2017

2017

4.50

36.93%

2018

4.50

7.17%

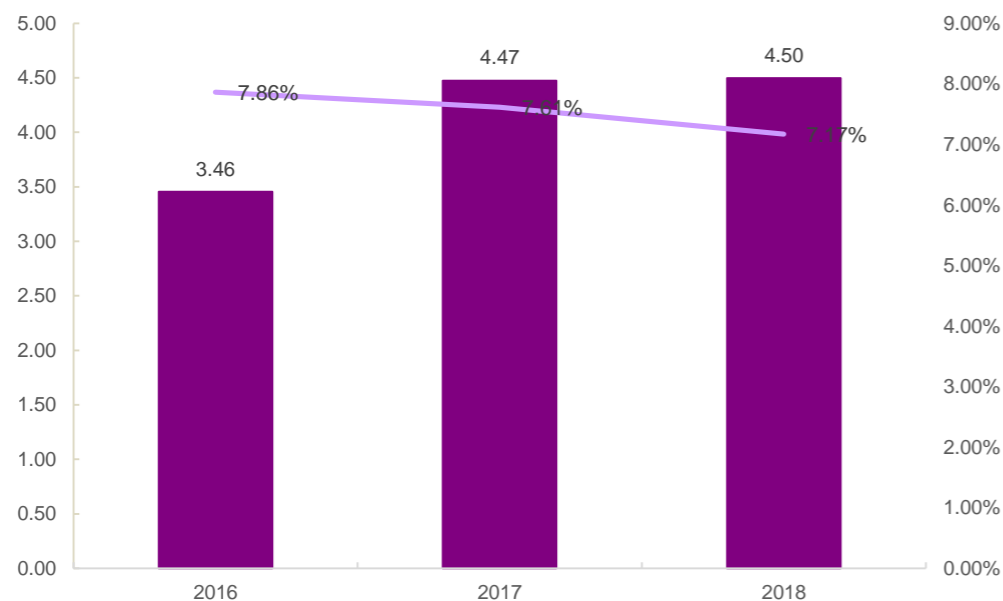
2019 6 30

7,937

641

2,290

36.93%



wind

	641	2290
		IC
		IC
	" "	" " " "

	2019	2018	2017	2016
	10,637.48	24,362.19	21,114.47	15,596.51
	879	872	796	691
	12.10	27.94	26.53	22.57

2018

80%

20%

IDM

2018

78%

5

2019	1		5,195.50	4.56%
	2		4,738.29	4.16%
	3		3,891.76	3.41%
	4		3,767.30	3.30%
	5		3,696.06	3.24%
				21,288.91

wind

2019	1		7,889.40	5.31%
	2	MPS International, Ltd	7,222.97	4.86%
	3		5,149.24	3.46%
	4		5,114.96	3.44%
	5	Diodes Incorporated	4,864.30	3.27%
				30,240.87

wind



1

2

3

4

5

3

MOEFET

2020 = + IC
422 153 4%

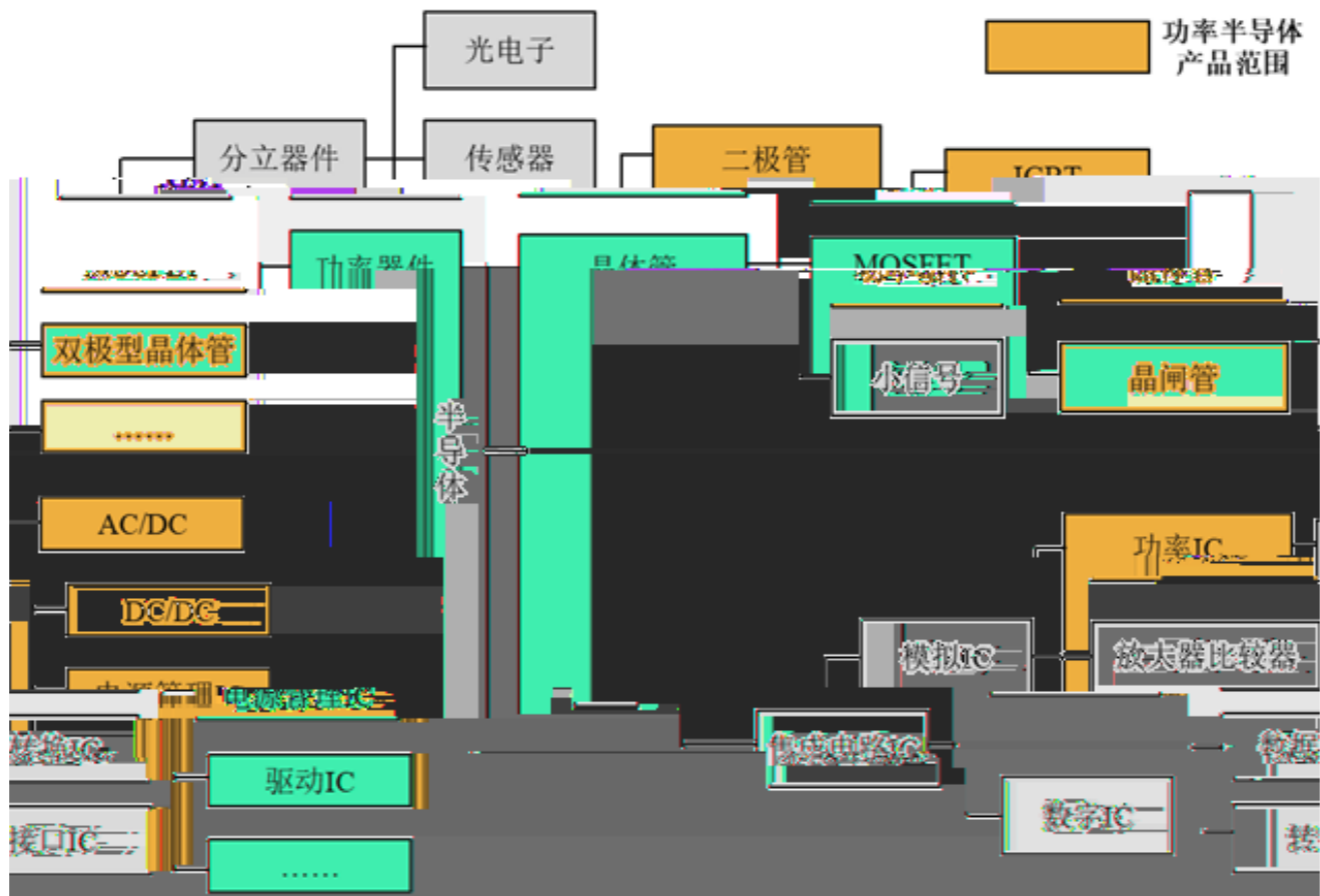
IDM MOEFET



= + IC

IC
IHS Markit MOSFET IGBT 5

= + IC



2020

422

153

4%

IHS Markit

2018

391

2021

441

4.1%

2018

138

9.5%

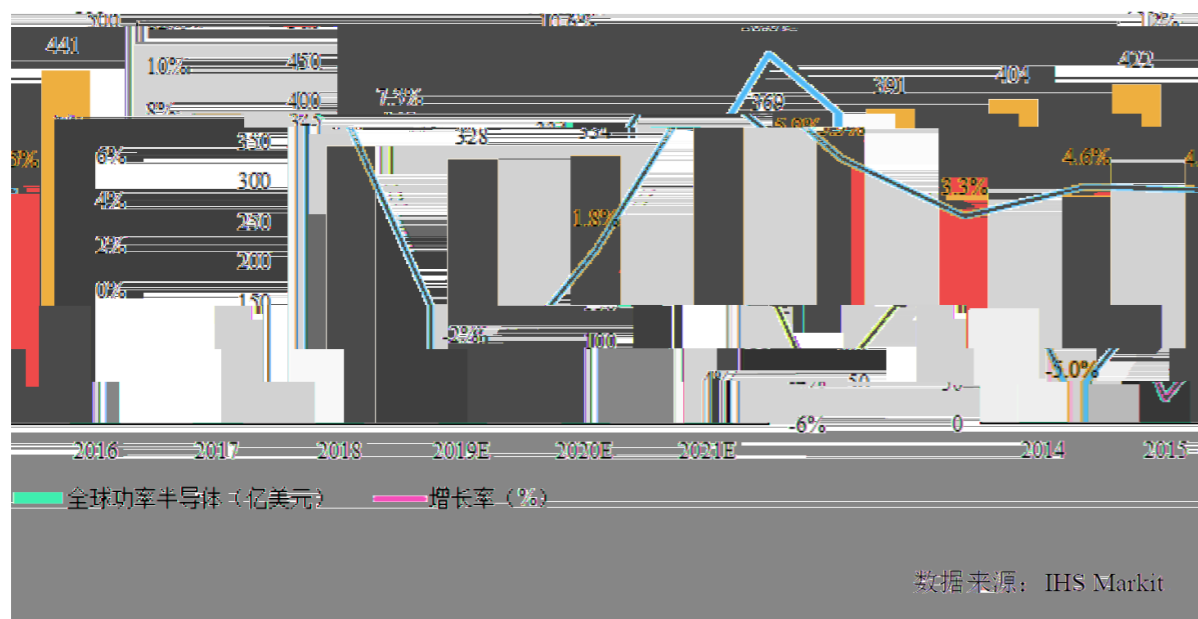
35%

2021

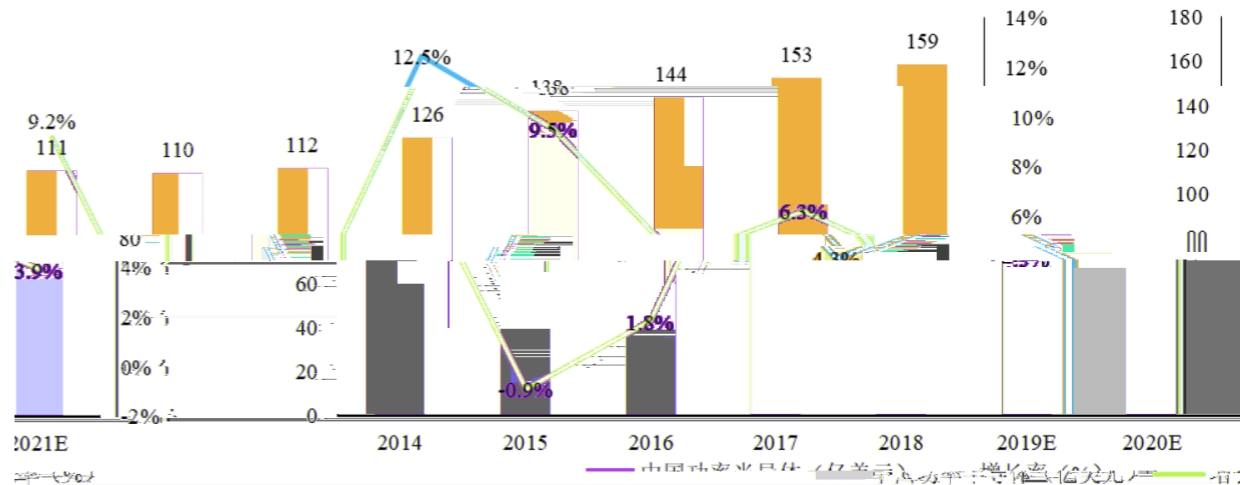
159

4.8%

2014-2021 全球功率半导体市场规模



2014-2021 年中国功率半导体市场规模及增长预测



数据来源: IHS Markit



光大电子
杨明辉 186-8946-4694
耿正 136-7166-5736

光大电子
杨明辉 186-8946-4694
耿正 136-7166-5736

光大电子



MOEFET

MOSFET MOS VDMOS MOSFET MOSFET MOSFET -100V 1500V
 MOSFET MOS MOS MOSFET
 IHS Markit MOSFET MOSFET

2018

	2018	MOSFET	
1	52	28.4%	
2	31	16.9%	
3	16	8.7%	
4	12	6.6%	
5	12	6.6%	
6	9	4.9%	
7	51	27.9%	
	183	100%	

IHS Markit

IDM

10

10

IDM

2018

2018

2018

		2018	
1		509	
2		248	
3		239	
4		225	
5		111	
6	()	107	
7		92	
8		66	
9		65	
10		63	IDM

2018

		2018
1		21.7
2		18.5
3		17.1
4		8.1
5		7.7
6		7.2
7		6.9
8		6.0
9		5.4
10		4.9

IDM

2018

IDM

IDM

1,100
MEMS

500 IC
IPM

BCD

2019 6 30

1,173

2,428
152

282

1,325

"

"

1

2

3

4

5

8

8

8

BCD

BCD

MEMS

8

MEMS

16,000

IC

MEMS

50% 20% 30%

1	8	15	50%
2		6	20%
3		3	10%
4		6	20%
		30	100%

1

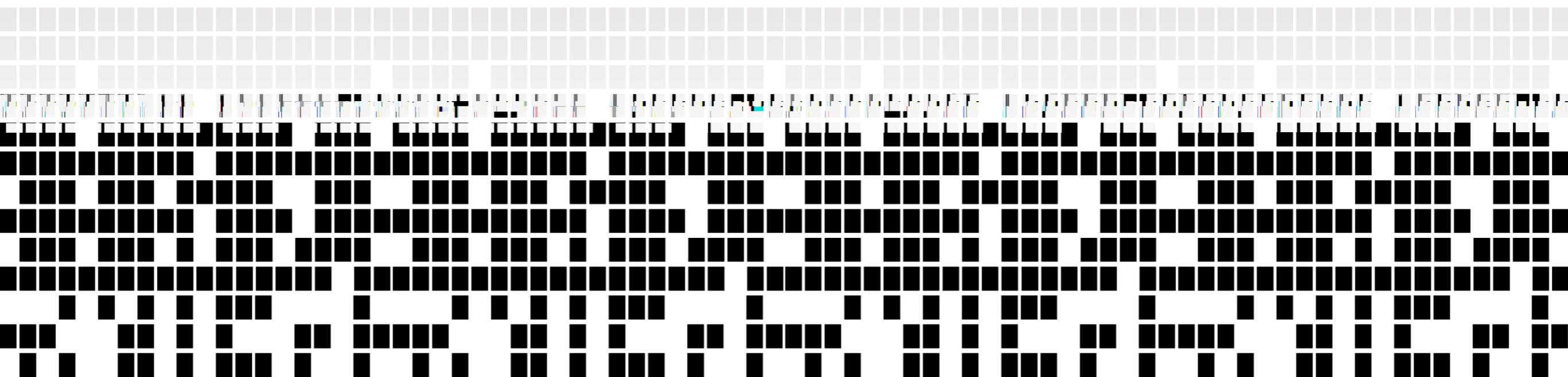
2

3

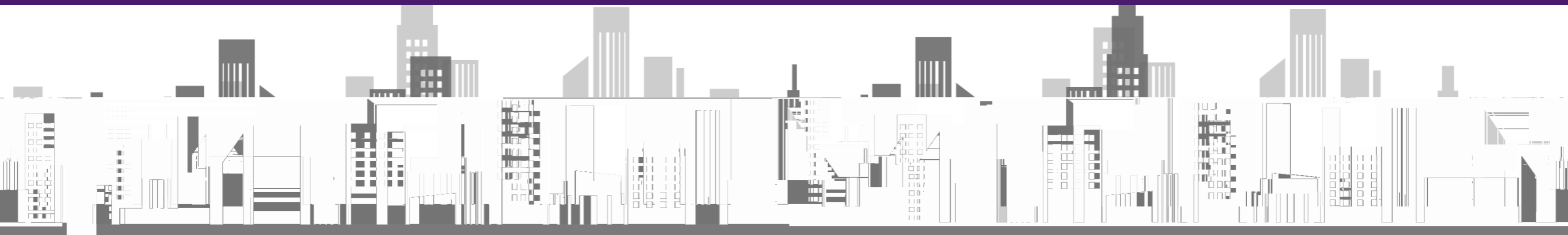
4

5





THANKYOU!



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021-52523862



wangjingwei@ebcn.com

0755-34945524

—	6-12		15%		
—	6-12		5%	15%	
—	6-12			-5%	5%
—	6-12		5%	15%	
—	6-12		15%		

A 300

" " 1996

" "